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In the Claims: ✓

Please cancel claims 1-6 without prejudice or disclaimer.

Please rewrite claims 7-9 as follows:

7. (Amended) An apparatus for fabricating a Group III-V nitride film by a MOCVD method, comprising:

a reactor in which a MOCVD reaction between a Group III raw material gas and a

Group V material gas is generated;

a susceptor to hold a substrate thereon installed in the reactor; and

a heater to heat the substrate to a predetermined temperature via the susceptor,

wherein

at least one of an interior wall of the reactor and the susceptor is coated with an $\text{Al}_a\text{Ga}_b\text{In}_c\text{N}$ ($a+b+c=1$, $a>0$) film, which is heated to a temperature of 1000°C or more.

8. (Amended) An apparatus as defined in claim 7, wherein the $\text{Al}_a\text{Ga}_b\text{In}_c\text{N}$ ($a+b+c=1$, $a>0$) film includes at least 50 atomic percent of Al ($a>0.5$) with respect to all of the Group III elements of the Periodic Table that are present in the film.

9. (Amended) An apparatus as defined in claim 8, wherein the $\text{Al}_a\text{Ga}_b\text{In}_c\text{N}$ ($a+b+c=1$, $a>0$) film is an AlN film.

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In the Abstract:

Attached hereto as page 10, pursuant to Rule 1.121(b)(1)(ii) is a clean version of the Abstract incorporating the changes being made thereto. Please replace the original Abstract with the new Abstract attached as page 10. Attached hereto as page 11, pursuant to Rule 1.121(b)(1)(iii), is a marked-up version of the Abstract showing changes being made thereto.